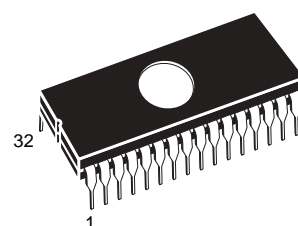


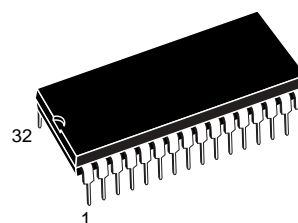
4 Mbit (512Kb x 8) UV EPROM and OTP EPROM

Feature summary

- 5V \pm 10% supply voltage in Read operation
- Access time: 35ns
- Low power consumption:
 - Active Current 30mA at 5MHz
 - Standby Current 100 μ A
- Programming voltage: 12.75V \pm 0.25V
- Programming time: 100 μ s/Word
- Electronic signature
 - Manufacturer Code: 20h
 - Device Code: 41h
- Packages
 - ECOPACK® compliant versions



FDIP32W (F)



PDIP32 (B)



PLCC32 (C)



TSOP32 (N) 8 x 20 mm

1 Summary description

The M27C4001 is a 4 Mbit EPROM offered in the two ranges UV (ultra violet erase) and OTP (one time programmable). It is ideally suited for microprocessor systems requiring large programs and is organised as 524,288 by 8 bits.

The FDIP32W (window ceramic frit-seal package) has a transparent lid which allows the user to expose the chip to ultraviolet light to erase the bit pattern. A new pattern can then be written to the device by following the programming procedure.

For applications where the content is programmed only one time and erasure is not required, the M27C4001 is offered in PDIP32, PLCC32 and TSOP32 (8 x 20 mm) packages.

In order to meet environmental requirements, ST offers the M27C4001 in ECOPACK® packages.

ECOPACK packages are Lead-free. The category of second Level Interconnect is marked on the package and on the inner box label, in compliance with JEDEC Standard JESD97. The maximum ratings related to soldering conditions are also marked on the inner box label.

ECOPACK is an ST trademark. ECOPACK specifications are available at: www.st.com.

Figure 1. Logic Diagram

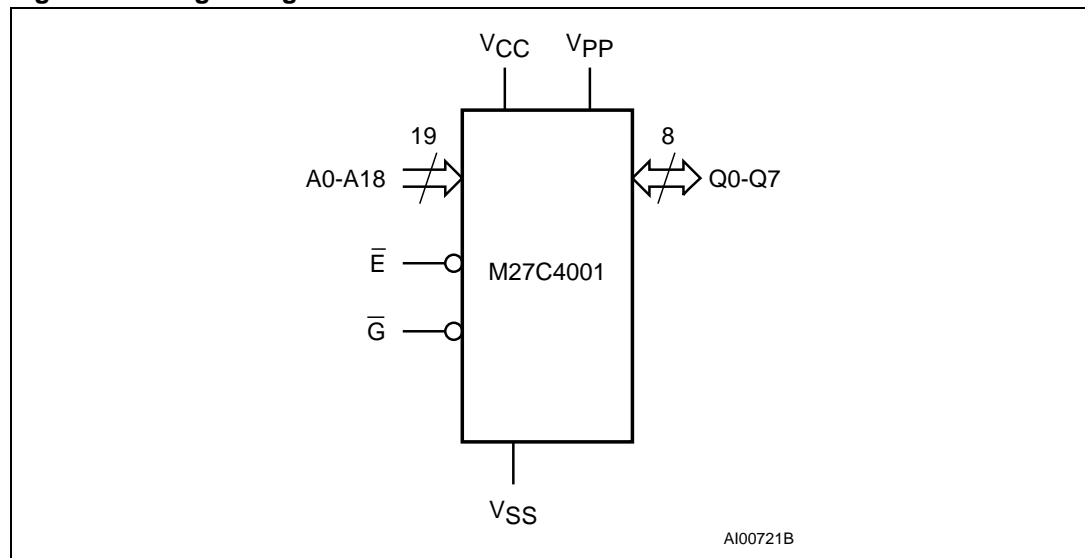


Table 1. Signal names

A0-A18	Address Inputs
Q0-Q7	Data Outputs
\bar{E}	Chip Enable
\bar{G}	Output Enable
V_{PP}	Program Supply
V_{CC}	Supply Voltage
V_{SS}	Ground

3 Maximum rating

Stressing the device above the rating listed in the Absolute Maximum Ratings table may cause permanent damage to the device. These are stress ratings only and operation of the device at these or any other conditions above those indicated in the Operating sections of this specification is not implied. Exposure to Absolute Maximum Rating conditions for extended periods may affect device reliability. Refer also to the STMicroelectronics SURE Program and other relevant quality documents.

Table 4. Absolute Maximum Ratings

Symbol	Parameter	Value	Unit
T_A	Ambient Operating Temperature ⁽¹⁾	-40 to 125	°C
T_{BIAS}	Temperature Under Bias	-50 to 125	°C
T_{STG}	Storage Temperature	-65 to 150	°C
$V_{IO}^{(2)}$	Input or Output Voltage (except A9)	-2 to 7	V
V_{CC}	Supply Voltage	-2 to 7	V
$V_{A9}^{(2)}$	A9 Voltage	-2 to 13.5	V
V_{PP}	Program Supply Voltage	-2 to 14	V

1. Depends on range.
2. Minimum DC voltage on Input or Output is -0.5V with possible undershoot to -2.0V for a period less than 20ns. Maximum DC voltage on Output is $V_{CC} + 0.5V$ with possible overshoot to $V_{CC} + 2V$ for a period less than 20ns.

Table 6. Capacitance (1) (2)

Symbol	Parameter	Test Condition	Min	Max	Unit
C _{IN}	Input Capacitance	V _{IN} = 0V		6	pF
C _{OUT}	Output Capacitance	V _{OUT} = 0V		12	pF

1. T_A = 25 °C, f = 1 MHz.
2. Sampled only, not 100% tested.

Table 7. Read Mode DC Characteristics(1) (2)

Symbol	Parameter	Test Condition	Min	Max	Unit
I _{LI}	Input Leakage Current	0V ≤ V _{IN} ≤ V _{CC}		±10	µA
I _{LO}	Output Leakage Current	0V ≤ V _{OUT} ≤ V _{CC}		±10	µA
I _{CC}	Supply Current	$\bar{E} = V_{IL}, \bar{G} = V_{IL},$ I _{OUT} = 0mA, f = 5MHz		30	mA
I _{CC1}	Supply Current (Standby) TTL	$\bar{E} = V_{IH}$		1	mA
I _{CC2}	Supply Current (Standby) CMOS	$\bar{E} > V_{CC} - 0.2V$		100	µA
I _{PP}	Program Current	V _{PP} = V _{CC}		10	µA
V _{IL}	Input Low Voltage		-0.3	0.8	V
V _{IH} ⁽³⁾	Input High Voltage		2	V _{CC} + 1	V
V _{OL}	Output Low Voltage	I _{OL} = 2.1mA		0.4	V
V _{OH}	Output High Voltage TTL	I _{OH} = -400µA	2.4		V
	Output High Voltage CMOS	I _{OH} = -100µA	V _{CC} - 0.7V		V

1. T_A = 0 to 70 °C or -40 to 85 °C; V_{CC} = 5V ± 5% or 5V ± 10%; V_{PP} = V_{CC}
2. V_{CC} must be applied simultaneously with or before V_{PP} and removed simultaneously or after V_{PP}.
3. Maximum DC voltage on Output is V_{CC} + 0.5V.

Table 8. Programming Mode DC Characteristics (1) (2)

Symbol	Parameter	Test Condition	Min	Max	Unit
I _{LI}	Input Leakage Current	0 ≤ V _{IN} ≤ V _{CC}		±10	µA
I _{CC}	Supply Current			50	mA
I _{PP}	Program Current	$\bar{E} = V_{IL}$		50	mA
V _{IL}	Input Low Voltage		-0.3	0.8	V
V _{IH}	Input High Voltage		2	V _{CC} + 0.5	V
V _{OL}	Output Low Voltage	I _{OL} = 2.1mA		0.4	V
V _{OH}	Output High Voltage TTL	I _{OH} = -400µA	2.4		V
V _{ID}	A9 Voltage		11.5	12.5	V

1. T_A = 25 °C; V_{CC} = 6.25V ± 0.25V; V_{PP} = 12.75V ± 0.25V.
2. V_{CC} must be applied simultaneously with or before V_{PP} and removed simultaneously or after V_{PP}.

Table 10. Read Mode AC Characteristics^{(1) (2)}

Symbol	Alt	Parameter	Test Condition	M27C4001						Unit
				-70		-80/-90		-10/-12/-15		
				Min	Max	Min	Max	Min	Max	
t_{AVQV}	t_{ACC}	Address Valid to Output Valid	$\bar{E} = V_{IL}, \bar{G} = V_{IL}$		70		80		100	ns
t_{ELQV}	t_{CE}	Chip Enable Low to Output Valid	$\bar{G} = V_{IL}$		70		80		100	ns
t_{GLQV}	t_{OE}	Output Enable Low to Output Valid	$\bar{E} = V_{IL}$		35		40		50	ns
$t_{EHQZ}^{(3)}$	t_{DF}	Chip Enable High to Output Hi-Z	$\bar{G} = V_{IL}$	0	30	0	30	0	30	ns
$t_{GHQZ}^{(3)}$	t_{DF}	Output Enable High to Output Hi-Z	$\bar{E} = V_{IL}$	0	30	0	30	0	30	ns
t_{AXQX}	t_{OH}	Address Transition to Output Transition	$\bar{E} = V_{IL}, \bar{G} = V_{IL}$	0		0		0		ns

1. $T_A = 0$ to 70 °C or -40 to 85 °C; $V_{CC} = 5V \pm 5\%$ or $5V \pm 10\%$; $V_{PP} = V_{CC}$

2. V_{CC} must be applied simultaneously with or before V_{PP} and removed simultaneously or after V_{PP} .

3. Sampled only, not 100% tested.

Figure 9. Programming and Verify Modes AC Waveforms

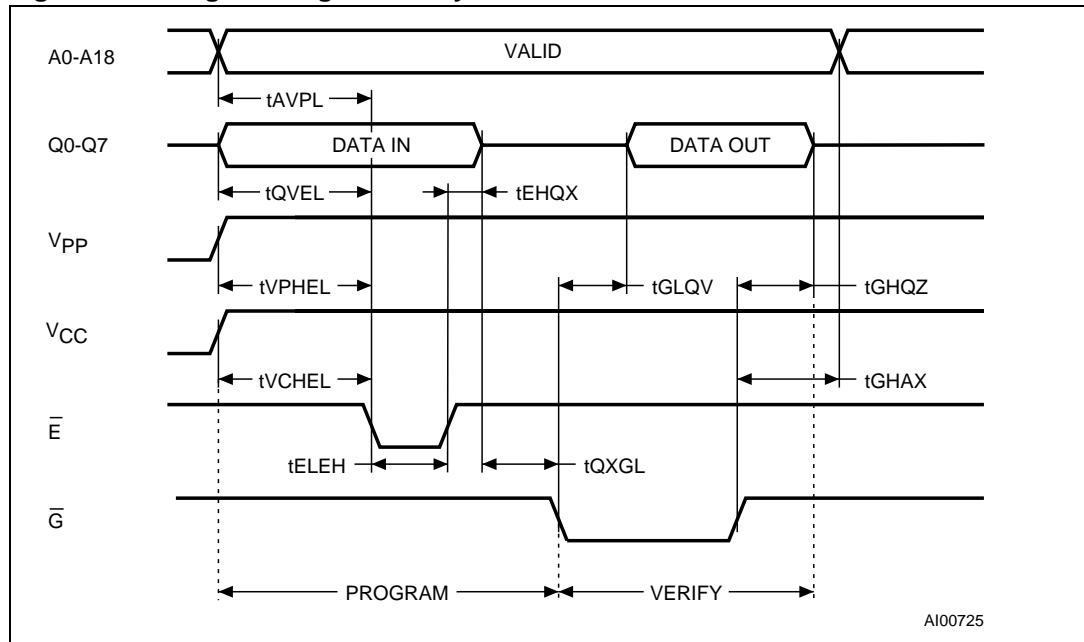
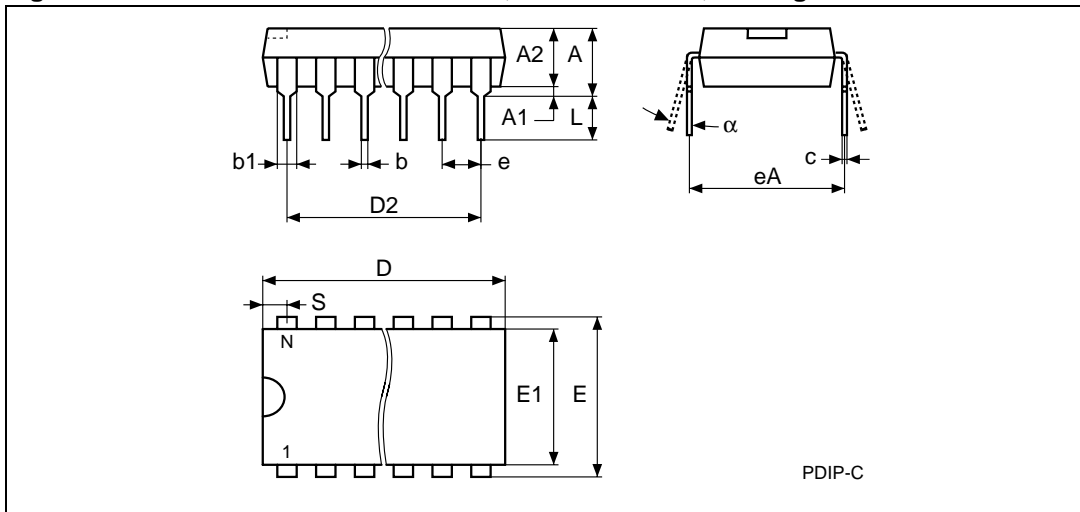


Table 11. Programming Mode AC Characteristics^{(1) (2) (3)}

Symbol	Alt	Parameter	Test Condition	Min	Max	Unit
t _{AVEL}	t _{AS}	Address Valid to Chip Enable Low		2		μs
t _{QVEL}	t _{DS}	Input Valid to Chip Enable Low		2		μs
t _{VPHEL}	t _{VPS}	V _{PP} High to Chip Enable Low		2		μs
t _{VCHL}	t _{VCS}	V _{CC} High to Chip Enable Low		2		μs
t _{ELEH}	t _{PW}	Chip Enable Program Pulse Width		95	105	μs
t _{EHQX}	t _{DH}	Chip Enable High to Input Transition		2		μs
t _{QXGL}	t _{OES}	Input Transition to Output Enable Low		2		μs
t _{GLQV}	t _{OE}	Output Enable Low to Output Valid			100	ns
t _{GHQZ}	t _{DFP}	Output Enable High to Output Hi-Z		0	130	ns
t _{GHAX}	t _{AH}	Output Enable High to Address Transition		0		ns

1. T_A = 25 °C; V_{CC} = 6.25V ± 0.25V; V_{PP} = 12.75V ± 0.25V
2. V_{CC} must be applied simultaneously with or before V_{PP} and removed simultaneously or after V_{PP}.
3. Sampled only, not 100% tested.

Figure 11. PDIP32 - 32 lead Plastic DIP, 600 mils width, Package Outline

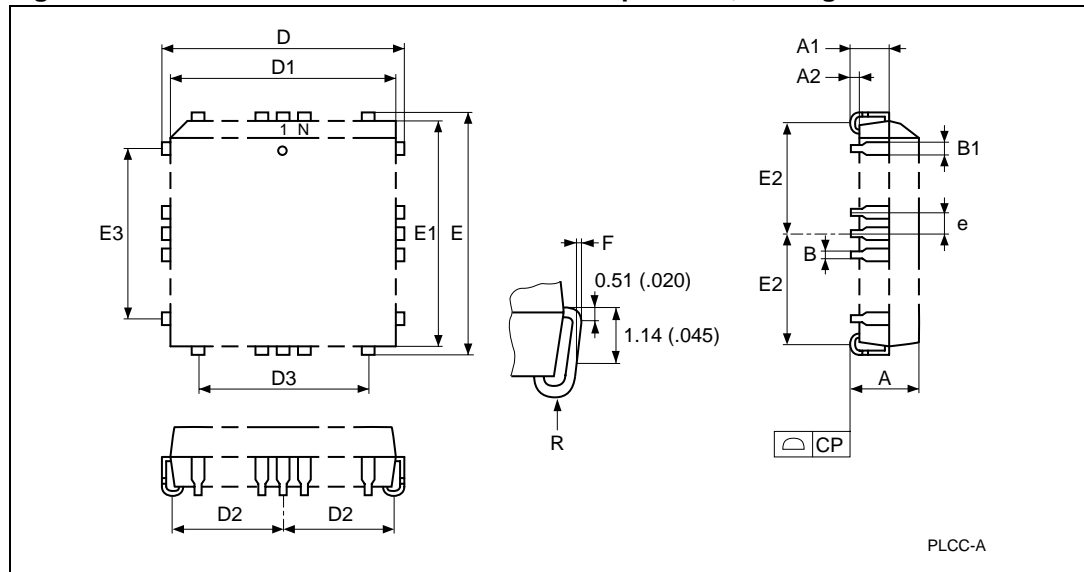


1. Drawing is not to scale.

Table 13. PDIP32 - 32 lead Plastic DIP, 600 mils width, package mechanical data

Symbol	millimeters			inches			
	Typ	Min	Max	Typ	Min	Max	
A			4.83			0.190	
A1		0.38			0.015		
A2	3.81			0.150			
b		0.41	0.53		0.016	0.021	
b1		1.14	1.65		0.045	0.065	
c		0.23	0.38		0.009	0.015	
D		41.78	42.29		1.645	1.665	
eA	15.24	–	–	0.600	–	–	
e	2.54	–	–	0.100	–	–	
E		15.24	15.88		0.600	0.625	
E1		13.46	13.97		0.530	0.550	
S		1.65	2.21		0.065	0.087	
L		3.05	3.56		0.120	0.140	
alpha		0°	15°		0°	15°	
N		32				32	

Figure 12. PLCC32 - 32 lead Plastic Leaded Chip Carrier, Package Outline



1. Drawing is not to scale.

Table 14. PLCC32 - 32 lead Plastic Leaded Chip Carrier, package mechanical data

Symbol	millimeters			inches		
	Typ	Min	Max	Typ	Min	Max
A		3.18	3.56		0.125	0.140
A1		1.53	2.41		0.060	0.095
A2		0.38	–		0.015	–
B		0.33	0.53		0.013	0.021
B1		0.66	0.81		0.026	0.032
CP			0.10			0.004
D		12.32	12.57		0.485	0.495
D1		11.35	11.51		0.447	0.453
D2		4.78	5.66		0.188	0.223
D3	7.62	–	–	0.300	–	–
E		14.86	15.11		0.585	0.595
E1		13.89	14.05		0.547	0.553
E2		6.05	6.93		0.238	0.273
E3	10.16	–	–	0.400	–	–
e	1.27	–	–	0.050	–	–
F		0.00	0.13		0.000	0.005
R	0.89	–	–	0.035	–	–
N	32			32		

6 Part numbering

Table 16. Ordering Information Scheme

Example:	M27C4001	-45	X	C	1
Device Type	M27				
Supply Voltage	C = 5V				
Device Function	4001 = 4 Mbit (512Kb x 8)				
Speed	-35 ⁽¹⁾ = 35 ns -45 ⁽¹⁾ = 45 ns -55 ⁽¹⁾ = 55 ns -70 = 70 ns -80 = 80 ns -90 = 90 ns -10 = 100 ns -12 = 120 ns -15 = 150 ns				
V_{CC} Tolerance	blank = ± 10% X = ± 5%				
Package	F = FDIP32W B = PDIP32 C = PLCC32 N = TSOP32: 8 x 20 mm				
Temperature Range	1 = 0 to 70 °C 6 = -40 to 85 °C				

1. High Speed, see AC Characteristics section for further information.

For a list of available options (Speed, Package, etc...) or for further information on any aspect of this device, please contact the STMicroelectronics Sales Office nearest to you.